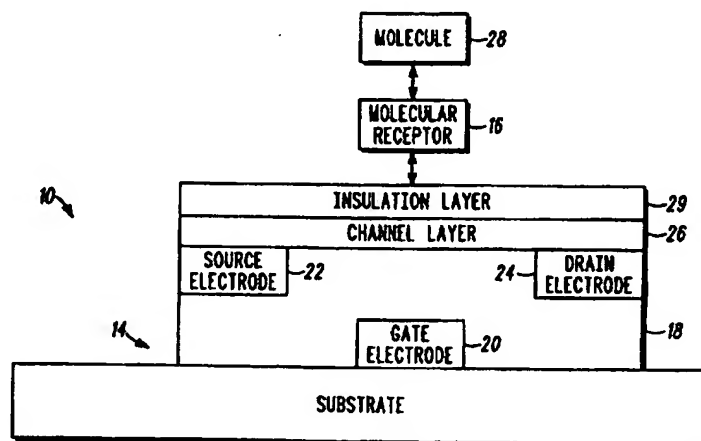




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| (21) International Application Number: PCT/US97/05660 (22) International Filing Date: 4 April 1997 (04.04.97) (30) Priority Data: 08/634,102 17 April 1996 (17.04.96) US (71) Applicant (for all designated States except US): MOTOROLA INC. [US/US]; 1303 East Algonquin Road, Schaumburg, IL 60196 (US). (72) Inventors; and (75) Inventors/Applicants (for US only): ACKLEY, Richard [US/US]; 317 Goat Hill Road, Lambertville, NJ 08530 (US). SHIEH, Chan-Long [US/US]; 6739 East Bar Z Lane, Paradise Valley, AZ 85253 (US). HARVEY, Thomas, B., III [US/US]; 8919 N. 80th Way, Scottsdale, AZ 85258 (US). (74) Agents: TOLER, Jeffrey, G. et al.; Motorola Inc., Intellectual Property Dept., 1303 East Algonquin Road, Schaumburg, IL 60196 (US). | | (81) Designated States: AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CU, CZ, DE, DK, EE, ES, FI, GB, GE, GH, HU, IL, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, TJ, TM, TR, TT, UA, UG, US, UZ, VN, YU, ARIPO patent (GH, KE, LS, MW, SD, SZ, UG), European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, ML, MR, NE, SN, TD, TG). Published <i>With international search report.</i> |

(54) Title: TRANSISTOR-BASED MOLECULAR DETECTION APPARATUS AND METHOD



(57) Abstract

A molecular detection apparatus (10) is formed by a substrate (12) which supports a binding site for receiving a molecular receptor (16), and a transistor integrated in the substrate. The transistor has a gate electrode (20), a source electrode (22), a drain electrode (24), and a semiconductive channel layer (26) which electrically couples the source electrode to the drain electrode. The semiconductive channel layer (26) is located proximate to the molecular receptor (16) so that a conductance between the source electrode and the drain electrode is modified by a charge associated with a molecule (28) which binds to the molecular receptor (16). Binding of the molecule to the molecular receptor (16) is sensed by a modified electrical characteristic of the transistor resulting from the charge associated with the molecule.

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10 TRANSISTOR-BASED MOLECULAR DETECTION APPARATUS AND METHOD

Field of the Invention

15 The present invention relates to molecular detection devices.

Background of the Invention

20 Recently, an increased effort has been directed toward the development of chips for molecular detection. In general, a molecular detection chip includes a substrate on which an array of binding sites is arranged. Each binding site (or hybridization site) has a respective molecular receptor which binds or hybridizes with a
25 molecule having a predetermined structure. A sample solution is applied to the molecular detection chip, and molecules in the sample bind or hybridize at one or more of the binding sites. The particular binding sites at which hybridization occurs are detected, and one or more
30 molecular structures within the sample are subsequently deduced.

Of great interest are molecular detection chips for gene sequencing. These chips, often referred to as DNA chips, utilize an array of selective binding sites each

0 having respective single-stranded DNA probes. A sample of
single-stranded DNA fragments, referred to as target DNA,
is applied to the DNA chip. The DNA fragments attach to
one or more of the DNA probes by a hybridization process.
By detecting which DNA probes have a DNA fragment
5 hybridized thereto, a sequence of nucleotide bases within
the DNA fragment can be determined.

To hasten the hybridization process, a local
concentration of target DNA can be increased at
predetermined sites using electric field enhancements.
10 Here, each site has an electrode associated therewith for
selectively generating an electric field thereby. The
electric field is generated by applying an electric
potential between an electrode at the site and a counter
electrode at a peripheral portion of the chip. To attract
15 DNA fragments to the site, the polarity of the electric
potential is selected to generate an electric field having
a polarity opposite to the charge of the DNA fragments.
To de-hybridize the site, an electric field having the
same polarity as the DNA fragments can be generated to
20 repel the DNA fragments from the site.

Various approaches have been utilized to detect a
hybridization event at a binding site. In one approach, a
radioactive marker is attached to each of a plurality of
molecules in the sample. The binding of a molecule to a
25 molecular receptor is then detectable by detecting the
radioactive marker.

Other approaches for detection utilize fluorescent
labels, such as fluorophores which selectively illuminate
when hybridization occurs. These fluorophores are
30 illuminated by a pump light source external to the
substrate. An external charge-coupled device (CCD) camera
is utilized to detect fluorescence from the illuminated
fluorophores.

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Brief Description of the Drawings

The invention is pointed out with particularity in the appended claims. However, other features of the invention will become more apparent and the invention will
5 be best understood by referring to the following detailed description in conjunction with the accompanying drawings in which:

FIG. 1 is a block diagram of an embodiment of a molecular detection apparatus in accordance with the
10 present invention;

FIG. 2 is a flow chart of an embodiment of a method of sensing a binding of a molecule to a molecular receptor at a binding site in a molecular detection apparatus;

FIG. 3 is a flow chart of an embodiment of a method
15 of sensing a modified electrical characteristic of the transistor;

FIG. 4 is a flow chart of another embodiment of a method of sensing a modified electrical characteristic of the transistor;

FIG. 5 is a flow chart of yet another embodiment of a method of sensing a modified electrical characteristic
20 of the transistor;

FIG. 6 schematically illustrates a differential pair formed by a first transistor and a second transistor;

FIG. 7 is a cross-sectional view of another
25 embodiment of an apparatus for sensing a binding of a molecule at a binding site in a molecular detection apparatus; and

FIGS. 8 and 9 illustrate a top view and a side view,
30 respectively, of an embodiment of an integrated molecular detection apparatus in accordance with the present invention.

0 Detailed Description of a Preferred Embodiment

Embodiments of the present invention advantageously provide a molecular detection apparatus which detects the binding or hybridization of a molecule to a molecular
5 receptor by sensing a charge associated with the molecule. A preferred embodiment utilizes a thin-film transistor integrated with a substrate to define a binding site. The thin-film transistor is utilized both to detect binding events and to control hybridization and de-hybridization.
10 The sensitivity of detection can be enhanced by forming a differential pair using the transistor and a second transistor at an unhybridized site.

FIG. 1 is a block diagram of an embodiment of a molecular detection apparatus 10 in accordance with the
15 present invention. The molecular detection apparatus 10 includes a substrate 12 which supports a binding site 14 for receiving a molecular receptor 16. In general, the molecular receptor 16 is selected in dependence upon a type of molecule which is to be detected. The molecular
20 receptor 16 typically includes a biological or synthetic molecule that has a specific affinity to the molecule to be detected. The molecular receptor 16 can include a chain of at least one nucleotide which hybridizes with a complementary chain of at least one nucleotide included in
25 the molecule. Here, for example, the molecular receptor 16 can include a DNA probe for detecting a corresponding, complementary DNA sequence in the molecule. It is noted, however, that the scope of the invention is not limited to sensing the hybridization of DNA molecules. For example,
30 embodiments of the present invention can be utilized to detect RNA hybridization and antibody-antigen binding events.

The molecular detection apparatus 10 further includes a transistor 18 integrated or fabricated in the

0 substrate 12. The transistor 18 has a gate electrode 20,
a source electrode 22, and a drain electrode 24. A
semiconductive channel layer 26 in the transistor 18
electrically couples the source electrode 22 to the drain
electrode 24. The semiconductive channel layer 26 is
5 located proximate to the binding site 14 so that a
conductance between the source electrode 22 and the drain
electrode 24 is modified by a charge associated with a
molecule 28 when the molecule 28 binds with the molecular
receptor 16. The binding of the molecule 28 to the
10 molecular receptor 16 is sensed by sensing a modified
electrical characteristic of the transistor 18 which
results from the charge associated with the molecule being
proximate to the semiconductive channel layer 26.

The charge associated with the molecule 28 can be
15 inherent in the molecule 28, such as the inherent charge
in a DNA molecule. The charge associated with the
molecule 28 may also result from a charged member attached
to the molecule 28. For example, the charge associated
with the molecule 28 can result from a charged bead being
20 attached to the molecule 28.

Various known technologies can be utilized to form
the transistor 18. In a preferred embodiment, the
transistor 18 is a thin-film transistor (TFT). Using
thin-film technology, the semiconductive channel layer 26
25 can be formed of an organic material which allows the
molecular receptor 16 to be bound directly to a surface of
the semiconductive channel layer 26. Alternatively, the
semiconductive channel layer 26 can be formed of silicon
(such as a-Si or poly-Si), in which case an insulation
30 layer 29 can be disposed between the molecular receptor 16
and a surface of the semiconductive channel layer 26 to
provide appropriate passivation. The insulation layer 29
can be in the form of a surface oxide layer.

0 To enhance the hybridization process, the apparatus
can include an attachment layer on which the molecular
receptor 16 is bound. The attachment layer is disposed
between the molecular receptor 16 and the surface of
either the semiconductive channel layer 26 or the
5 insulation layer 29.

FIG. 2 is a flow chart of an embodiment of a method
of sensing a binding of a molecule to a molecular receptor
at a binding site in a molecular detection apparatus. As
indicated by block 30, the method includes a step of
10 providing a transistor having a semiconductive channel
layer located proximate to the molecular receptor so that
a conductance between a source electrode and a drain
electrode is modified by a charge associated with the
molecule when the molecule hybridizes with the molecular
15 receptor. This step can be performed by utilizing an
embodiment of a molecular detection apparatus as described
herein.

As indicated by block 32, the method includes a step
of sensing a modified electrical characteristic of the
20 transistor which results from the charge associated with
the molecule being proximate to the semiconductive channel
layer upon binding. This step of sensing the modified
electrical characteristic can be performed in a variety of
ways, three of which being described below.

25 FIG. 3 is a flow chart of an embodiment of a method
of sensing a modified electrical characteristic of the
transistor. As indicated by block 40, the method includes
a step of biasing the transistor in a predetermined manner
prior to the binding of the molecule with the molecular
30 receptor. Here, a respective, predetermined voltage level
is applied to each of the gate electrode, the drain
electrode, and the source electrode of the transistor.

As indicated by block 42, a step of measuring a
first channel current between the drain electrode and the

0 source electrode is performed prior to the binding of the molecule with the molecular receptor. The first channel current results from the biasing of the transistor performed in the previous step.

After measuring the first channel current, the
5 molecule is allowed to hybridize or bind with the molecular receptor. As indicated by block 44, the binding can be field-enhanced by performing a step of applying a first voltage to at least one of the gate electrode, the source electrode, and the drain electrode. The first
10 voltage is selected to generate an electric field which attracts the molecule to the binding site.

After hybridization, an optional step of dehybridizing any unwanted molecules from the binding site can be performed. Specifically, as indicated by block 46,
15 a step of dehybridization can be performed by applying a second voltage to at least one of the gate electrode, the source electrode, and the drain electrode. The second voltage is selected to provide an electric field which repels unwanted molecules from the binding site. The
20 unwanted molecules can include partially-bound molecules, for example.

As indicated by block 48, a step of re-biasing the transistor is performed. Here, the transistor is biased in the same predetermined manner as in the step indicated
25 by block 40.

As indicated by block 50, a step of measuring a second channel current between the drain electrode and the source electrode is performed after the binding of the molecule with the molecular receptor. The second channel
30 current results from the biasing of the transistor performed in the previous step. Preferably, the first channel current and the second channel current are measured for a fixed voltage applied to the gate electrode.

0 The modified electrical characteristic is sensed by
a step of detecting a difference between the first channel
current and the second channel current, indicated by block
52. For example, the modified electrical characteristic
may be determined when a difference between the first
5 channel current and the second channel current is beyond a
predetermined threshold.

FIG. 4 is a flow chart of another embodiment of a
method of sensing a modified electrical characteristic of
the transistor. As indicated by block 60, the method
10 includes a step of biasing the transistor in a
predetermined manner. Here, a respective, predetermined
voltage level is applied to each of the drain electrode
and the source electrode of the transistor.

As indicated by block 62, a step of determining a
15 voltage for the gate electrode to produce a predetermined
channel current is performed. In one embodiment, the
predetermined channel current is selected to be near zero.
Here, the voltage applied to the gate electrode is varied
to determine a threshold voltage which nulls out the
20 channel current. The threshold voltage which nulls the
channel current is proportional to the amount of charge
incorporated into the channel layer by the binding. It is
noted that the predetermined channel current need not be
near zero in alternative embodiments.

25 The modified electrical characteristic is sensed by
a step, indicated by block 64, of detecting a difference
between a predetermined voltage level and the voltage
determined in the above-described step. The predetermined
voltage level can be, for example, a voltage which
30 produces the predetermined channel current before
hybridization. Hence, the modified electrical
characteristic may be determined when the gate voltage
(post-hybridization) which produces the predetermined
channel current is beyond a predetermined threshold.

0 FIG. 5 is a flow chart of yet another embodiment of
a method of sensing a modified electrical characteristic
of the transistor. As indicated by block 70, the method
includes a step of providing a second transistor which is
substantially similar to the transistor at the binding
5 site. The second transistor, however, is located at an
unhybridized site on the molecular detection apparatus.
The second transistor is electrically connected with the
transistor to form a differential pair. As indicated by
block 71, a step of detecting a signal, produced by the
10 differential pair, indicative of a binding of the molecule
at the binding site is performed.

FIG. 6 schematically illustrates a differential pair
72 formed by a first transistor 73 and a second transistor
74. The first transistor 73 is located at a binding site
15 while the second transistor 74 is located at an
unhybridized site. Physically, the first transistor 73
and the second transistor 74 can be located adjacent one
another on a substrate. The differential pair is formed
by coupling a source electrode 75 of the first transistor
20 73 to a source electrode 76 of the second transistor 74.

A binding event can be detected by applying a common
voltage to gate electrodes 77 and 78, and detecting a
difference in channel currents between the first
transistor 73 and the second transistor 74.
25 Alternatively, the binding event can be detected by
detecting a non-zero offset voltage between the gate
electrodes 77 and 78 which produces equal channel currents
for the first transistor 73 and the second transistor 74.

FIG. 7 is a cross-sectional view of another
30 embodiment of an apparatus for sensing a binding of a
molecule at a binding site in a molecular detection
apparatus. This embodiment utilizes a thin-film
transistor 80 formed on a substrate 82. Disposed on a top
surface of the substrate 82 are a gate electrode 84 and an

0 insulation layer 86. A source electrode 88, a drain electrode 90, and a channel layer 92 are formed on a top surface of the insulation layer 86.

A molecular receptor, such as a single-stranded DNA molecule 94, is located in proximity to the channel layer
5 92. As illustrated, the single-stranded DNA molecule 94 can be attached directly to a surface of the channel layer 92. As described earlier, the channel layer 92 can be formed of an organic material which allows the single-stranded DNA molecule 94 to be directly attached to the
10 surface. Here, the organic material is selected to be compatible with the DNA species and to optimize the attachment of DNA fragments to the surface.

By burying the gate electrode 84, the source electrode 88, and the drain electrode 90 beneath the
15 channel layer 92, difficulties associated with potential-induced denaturation at the electrodes are prevented.

FIGS. 8 and 9 illustrate a top view and a side view, respectively, of an embodiment of an integrated molecular detection apparatus in accordance with the present
20 invention. The integrated molecular detection apparatus includes an array of thin-film transistors 100 fabricated on a top surface of a substrate 102. The thin-film transistors 100 can be formed in a manner similar to that used to construct active matrix displays.

25 Each of the thin-film transistors 100 is located proximate to a respective one of plurality of binding sites 104. Specific DNA probes are deposited onto each of the thin-film transistors 100. The DNA probes can be deposited using conventional robotic dispensing
30 techniques, or can be bound specifically into a channel of the thin-film transistors 100 using binding techniques known in the art.

In operation as a sequencer or a diagnostic tool, DNA sequences in a sample analyte hybridize onto selective

0 ones of the binding sites 104. Field-assisted or
thermally-assisted hybridization techniques can be
utilized to enhance the hybridization process. After
hybridization, unwanted sequences with only partial
5 switching appropriate biases onto at least one electrode
of the thin-film transistors 100. Alternatively, thermal
desorption can be utilized to dehybridize unwanted
sequences.

Thereafter, each of the thin-film transistors 100 is
10 biased for transistor operation. As described earlier, a
gate voltage for each of the thin-film transistors 100 can
be varied to null out a respective channel current. The
gate voltage required to null out the respective channel
current is proportional to an amount of charge
15 incorporated in the thin-film transistor. The value of
the gate voltage can be read-out through the active
matrix. As previously described, alternative approaches
to detecting binding events include, but are not limited
to, detecting a variation in channel current (measured
20 before and after hybridization) for a fixed gate voltage,
and detecting a signal produced by a differential pair of
thin-film transistors.

Thus, there has been described herein a concept, as
well as several embodiments including preferred
25 embodiments of a transistor-based molecular detection
apparatus and method.

Because the various embodiments of the present
invention detect a binding event by sensing a charge
associated with a target molecule, they provide a
30 significant improvement in that a transistor integrated in
the molecular detection apparatus can be utilized to
electronically detect the target molecule. To improve
detection, the charge associated with the target molecule

0 can be enhanced by attaching a charged bead to the target molecule.

Additionally, the various embodiments of the present invention as herein-described utilize electrodes in the transistor to perform field-assisted hybridization and
5 dehybridization.

It will be apparent to those skilled in the art that the disclosed invention may be modified in numerous ways and may assume many embodiments other than the preferred form specifically set out and described above.

10 Accordingly, it is intended by the appended claims to cover all modifications of the invention which fall within the true spirit and scope of the invention.

What is claimed is:

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Claims

1. A molecular detection apparatus comprising:
a substrate which supports a binding site for
receiving a molecular receptor; and
5 a transistor integrated with the substrate, the
transistor having a gate electrode, a source electrode, a
drain electrode, and a semiconductive channel layer which
electrically couples the source electrode to the drain
electrode, the semiconductive channel layer located
10 proximate to the binding site so that a conductance
between the source electrode and the drain electrode is
modified by a charge associated with a molecule which
binds to the molecular receptor;
wherein binding of the molecule to the molecular
15 receptor is sensed by a modified electrical characteristic
of the transistor resulting from the charge associated
with the molecule.
2. The apparatus of claim 1 wherein the charge
20 associated with the molecule is in a charged member
attached to the molecule.
3. The apparatus of claim 1 wherein the molecular
receptor is bound directly to a surface of the
25 semiconductive channel layer.
4. The apparatus of claim 1 further comprising an
attachment layer on which the molecular receptor is bound,
the attachment layer disposed between the molecular
30 receptor and a surface of the semiconductive channel
layer.

0 5. The apparatus of claim 1 further comprising a
second transistor substantially similar to the transistor,
the second transistor located at an unbound site on the
substrate, wherein the second transistor is electrically
connected with the transistor to form a differential pair
5 which provides a signal indicative of detecting the
molecule.

6. A method of sensing a binding of a molecule with
a molecular receptor at a binding site in a molecular
10 detection apparatus, the method comprising the steps of:
providing a transistor having a semiconductive
channel layer which electrically couples a source
electrode to a drain electrode, the semiconductive channel
layer located proximate to the molecular receptor so that
15 a conductance between the source electrode and the drain
electrode is modified by a charge associated with the
molecule when the molecule binds with the molecular
receptor, the transistor further including a gate
electrode; and
20 sensing a modified electrical characteristic of the
transistor which results from the charge associated with
the molecule when the molecule binds with the molecular
receptor.

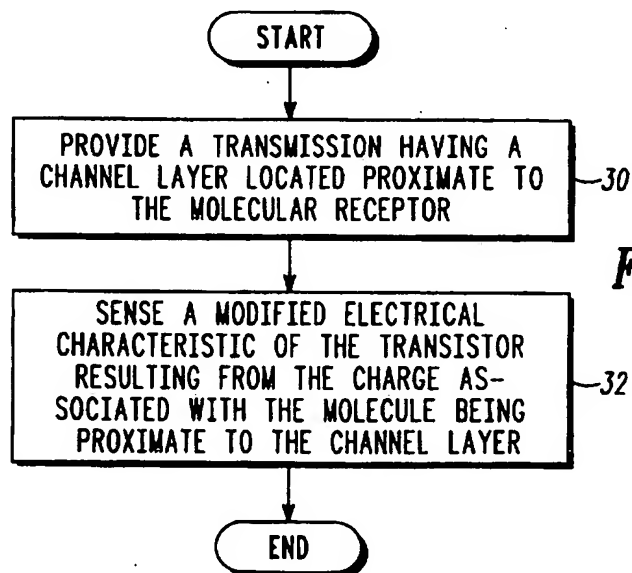
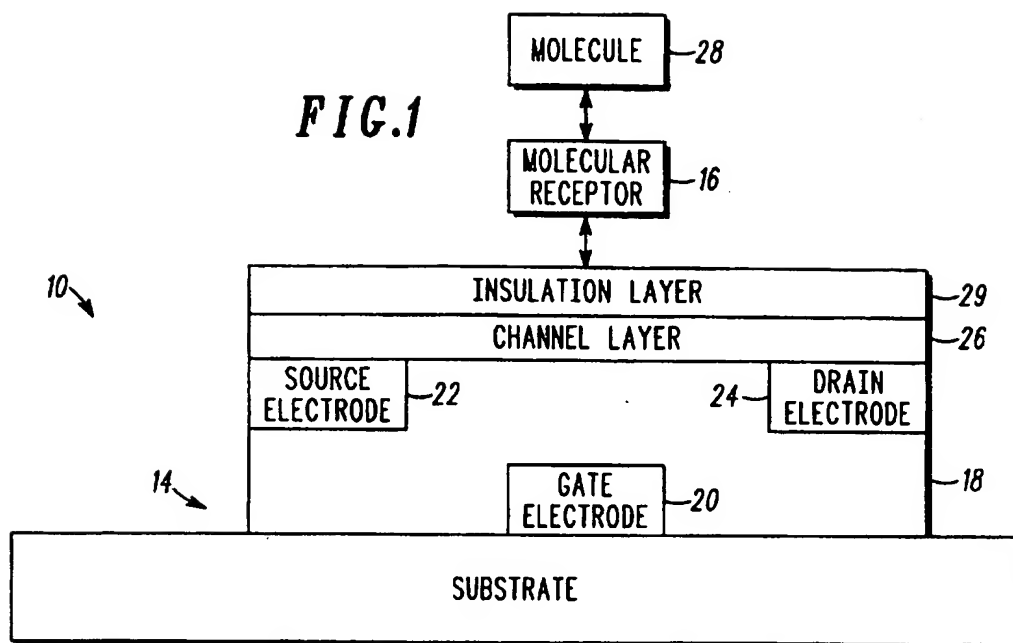
25 7. The method of claim 6 wherein the step of
sensing the modified electrical characteristic of the
transistor includes:
measuring a first channel current prior to binding
of the molecule with the molecular receptor;
30 measuring a second channel current after binding of
the molecule with the molecular receptor;
detecting a difference between the first channel
current and the second channel current.

0 8. The method of claim 6 wherein the transistor is
a thin film transistor.

 9. The method of claim 8 wherein the molecular
receptor is bound directly to a surface of the
5 semiconductive channel layer.

 10. The method of claim 6 further comprising the
step of providing a second transistor substantially
similar to the transistor, the second transistor located
10 at an unbound site on the molecular detection apparatus,
wherein the second transistor is electrically connected
with the transistor to form a differential pair to sense
the molecule.

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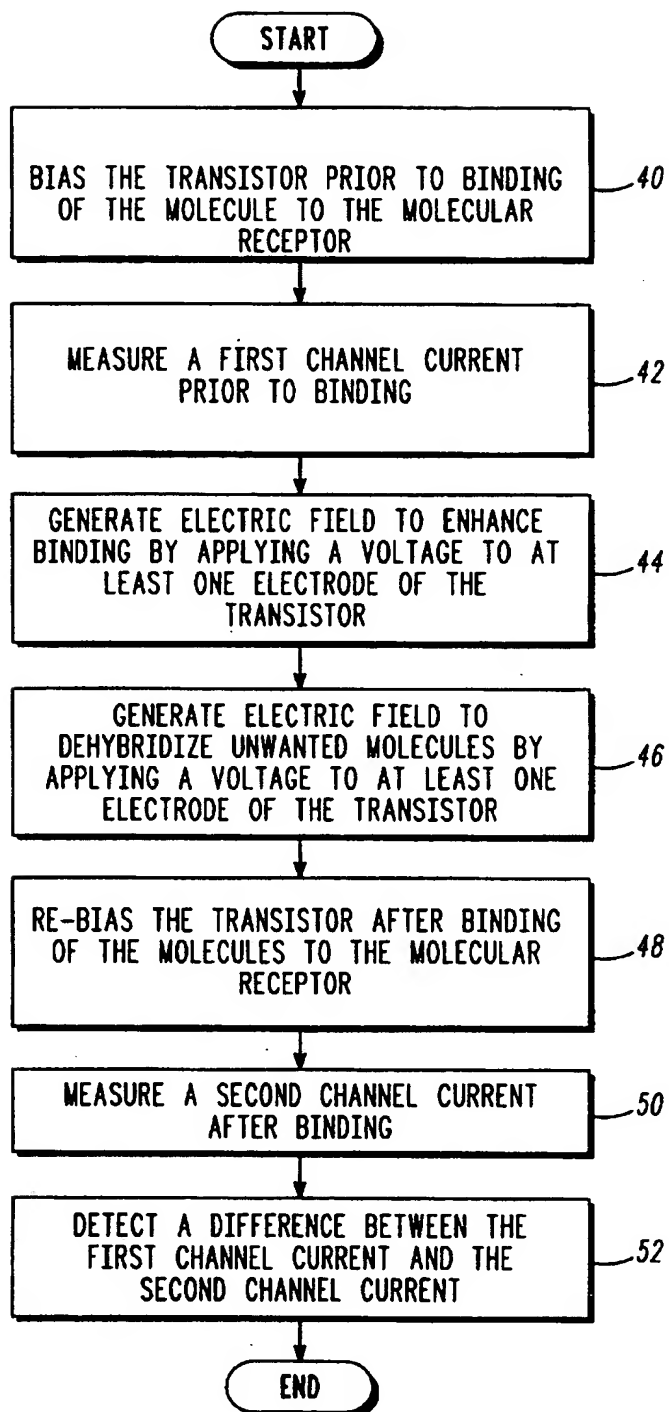
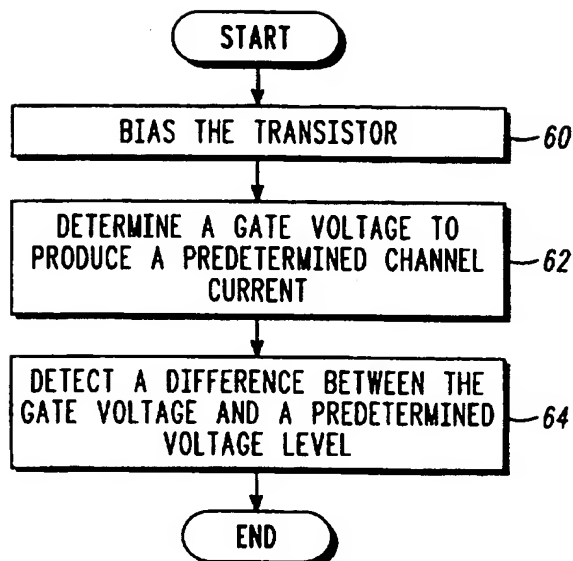
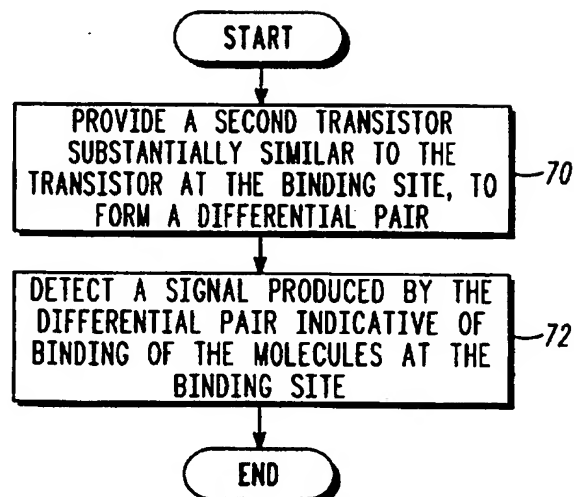


FIG.3

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**FIG. 4****FIG. 5**

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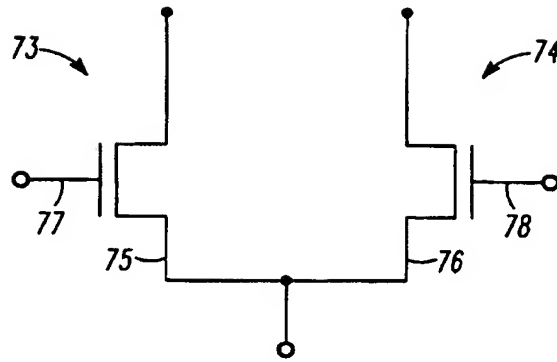


FIG.6

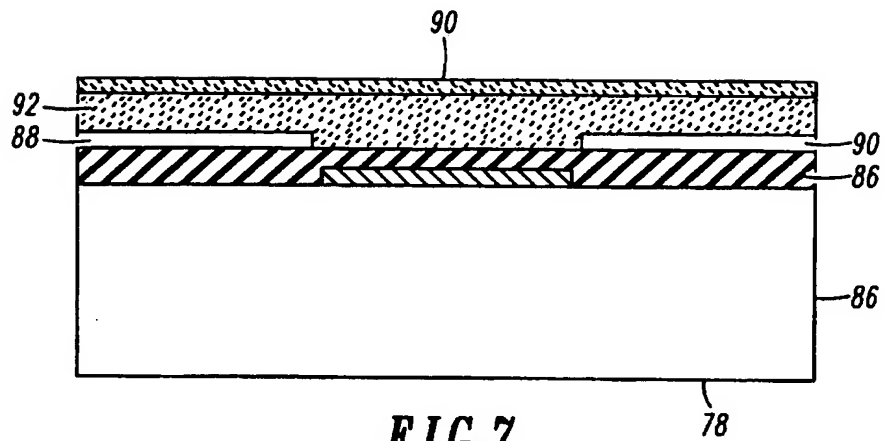


FIG.7

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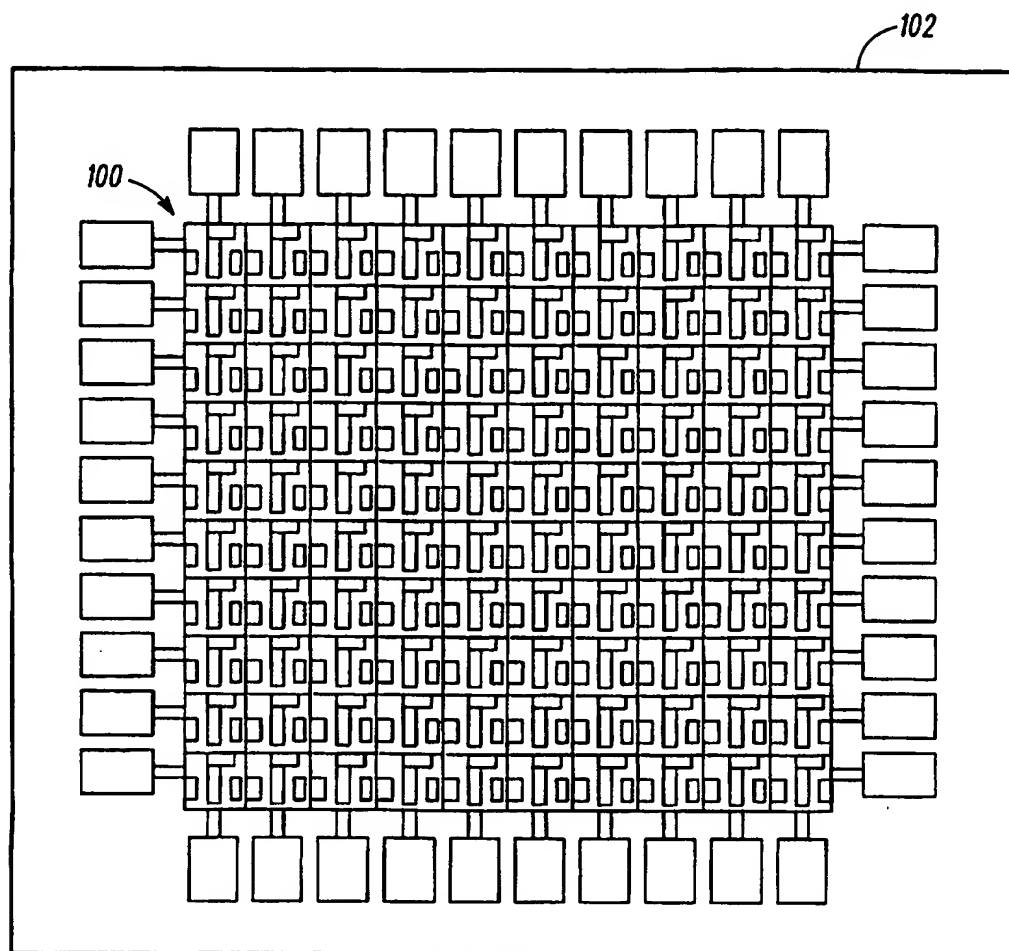


FIG. 8

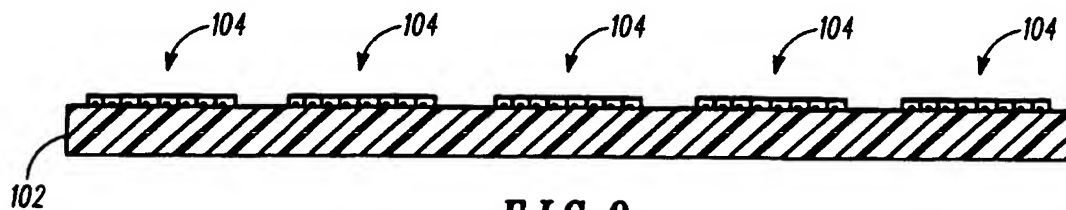


FIG. 9

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US97/05660

| A. CLASSIFICATION OF SUBJECT MATTER IPC(6) : Please See Extra Sheet. US CL : Please See Extra Sheet. According to International Patent Classification (IPC) or to both national classification and IPC | | | | |
|---|--|---|---|--|
| B. FIELDS SEARCHED Minimum documentation searched (classification system followed by classification symbols) U.S. : 435/6, 5, 7.1, 7.2, 7.9; 422/88, 82.01; 436/500; 518, 524, 525; 437/40 Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Electronic data base consulted during the international search (name of data base and, where practicable, search terms used) Please See Extra Sheet. | | | | |
| C. DOCUMENTS CONSIDERED TO BE RELEVANT | | | | |
| Category* | Citation of document, with indication, where appropriate, of the relevant passages | Relevant to claim No. | | |
| Y | US 5,391,507 A (KWASNICK et al) 21 February 1995, see abstract. | 1-10 | | |
| Y | US 5,328,847 A (CASE et al) 12 July 1994, see entire document. | 1-10 | | |
| Y | US 4,490,216 A (MCCONNELL) 25 December 1984, see entire document. | 1-10 | | |
| Y, P | US 5,527,670 A (STANLEY) 18 June 1996, see abstract. | 1-10 | | |
| A, P | US 5,532,128 A (EGGERS et al) 02 July 1996, see entire document. | 1-10 | | |
| Y | US 5,071,733 A (UEKITA et al) 10 December 1991, see column 29, lines 54-65 and column 31. | 1-10 | | |
| <input type="checkbox"/> Further documents are listed in the continuation of Box C. <input type="checkbox"/> See patent family annex. | | | | |
| <table border="0"> <tr> <td> * Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier document published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed </td> <td> "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "Z" document member of the same patent family </td> </tr> </table> | | | * Special categories of cited documents: "A" document defining the general state of the art which is not considered to be of particular relevance "E" earlier document published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed | "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "Z" document member of the same patent family |
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| Date of the actual completion of the international search 20 MAY 1997 | | Date of mailing of the international search report 11 JUL 1997 | | |
| Name and mailing address of the ISA/US Commissioner of Patents and Trademarks Box PCT Washington, D.C. 20231 Facsimile No. (703) 305-3230 | | Authorized officer DIANNE REES Telephone No. (703) 308-0196 | | |

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US97/05660

A. CLASSIFICATION OF SUBJECT MATTER:
IPC (6):

C12Q 1/68, 1/70; G01N 33/53, 30/96, 27/00, 33/543, 33/551; 33/553; H01L 21/265

A. CLASSIFICATION OF SUBJECT MATTER:
US CL :

435/6, 5, 7.1, 7.2, 7.9; 422/88, 82.01; 436/500; 518, 524, 525; 437/40

B. FIELDS SEARCHED

Electronic data bases consulted (Name of data base and where practicable terms used):

APS, BIOSIS, BIOTECHDS, BIOTECHABS, BIOBUSINESS, CABA, CAPLUS, CANCERLIT, DRUGU , EMBASE, EUROPATFULL, IFIPAT, JAPIO, MEDLINE, USPATFULL, TOXLINE, TOXLIT, SCISEARCH, WPIDS
search terms: transistor, electrode, frequency, receptors, or ligands, probes, oligonucleotides, DNA, nucleic acids, polynucleotides, gate electrode, source electrode, semiconductive, charge, binding, hybridization or hybridisation, channel current, thin film transistors